

**AMENDMENT TO THE CLAIMS**

This listing of the claims will replace all prior versions, and listings, of claims in the application.

**What Is Claimed Is:**

**1. (currently amended)** A method for forming a semiconductor device comprising the steps of:

depositing a monoatomic metal film ~~including a metal~~ on a base by using a metal source including a compound containing said metal and no oxygen; and

depositing a metal oxide film including oxide of said metal on said monoatomic metal film by using a CVD technique.

**2. (currently amended)** The method according to claim 1, further comprising, before said monoatomic metal film depositing step, the step of supplying oxidizing gas onto a surface of said base.

**3. (original)** The method according to claim 2, wherein said oxidizing gas includes heated H<sub>2</sub>O.

**4. (original)** The method according to claim 2, wherein said oxidizing gas includes at least one gas selected from the group consisting 0<sub>2</sub>, active oxygen, ozone, and N<sub>2</sub>O.

**5. (currently amended)** The method according claim 1, further comprising, before said monoatomic metal film depositing step, the step of supplying hydrofluoric acid onto a surface of said base.

**6. (original)** The method according to claim 1, wherein said metal source includes at least one said compound selected from the group consisting of  $TaCl_5$ ,  $TaF_5$  and  $Ta(N(C_2H_5)_2)_3$ , and said metal oxide film is tantalum oxide.

**7. (original)** The method according to claim 1, wherein said metal source includes  $Al(CH_3)_3$ , and said metal oxide is titanium oxide.

**8. (original)** The method according to claim 1, wherein said metal source includes  $TiCl_4$  or  $Ti(N(CH_3)_2)_4$  and said metal oxide is titanium oxide.

**9. (original)** The method according to claim 1, wherein said metal source includes at least one said compound selected from the group consisting of  $Hf(NCH_3)_2)_4$ ,  $Hf(N(C_2H_5)(CH_3))_4$  and  $Hf(C_2H_5)_2)_4$ , and said metal oxide is hafnium oxide.

**10. (original)** The method according to claim 1, wherein said metal source includes at least one said compound selected from the group consisting of  $NbCl_5$ ,  $NbF_5$  and  $Nb(N(C_2H_5)_2)_3$ , and said metal oxide is niobium oxide.

**11. (currently amended)** The method according to claim 1, further comprising, between said monoatomic metal film depositing step and said metal oxide film depositing step, the step of supplying oxidizing gas onto a surface of said monoatomic metal film.

**12. (original)** The method according to claim 12, wherein said base is either silicon substrate, polysilicon film, silicon nitride film or a metallic film.

**13. (original)** The method according to claim 1, further comprising the step of forming a conductive film on said metal oxide film, wherein said steps are used for forming a capacitor including said base as a bottom electrode, said metal oxide film as a capacitor insulation film, and said conductive film as a top electrode.

**14. (currently amended)** A method for forming a semiconductor device comprising:

depositing a monoatomic metal film ~~including a metal~~ on a base in an oxygen-free environment; and

depositing a metal oxide film including an oxide of the metal on the monoatomic metal film using a CVD technique.

**15. (previously presented)** The method of claim 14, wherein the semiconductor device is adapted to function as a capacitor.

**16. (currently amended)** The method of claim 14, wherein the depositing of the monoatomic metal film including the metal includes using a metal source including a compound containing the metal.

**17. (currently amended)** A semiconductor device formed by a method, the method comprising:

depositing a monoatomic metal film ~~including a metal~~ on a base in an oxygen-free environment; and

depositing a metal oxide film including an oxide of the metal on the monoatomic metal film using a CVD technique.

**18. (previously presented)** The semiconductor device of claim 17, wherein the semiconductor device is adapted to function as a capacitor.